



DFW

In re the Application of:

Katsutoshi Izumi et al

Group Art Unit: 2813

Serial No.: 10/802,806

Examiner: Heather Anne Doty

Filed: March 18, 2004

P.T.O. Confirmation No.: 5100

For: MANUFACTURING METHOD FOR BURIED INSULATING LAYER-TYPE
SEMICONDUCTOR SILICON CARBIDE SUBSTRATE

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: December 8, 2005

Sir:

In response to the Office Action dated September 13, 2005, please amend the
above-identified application as set forth below:

Amendments to the Claims begin on page two of this paper.

Remarks begin on page five of this paper.